

Power Schottky rectifier

Main product characteristics

$I_{F(AV)}$	2 x 20 A
V_{RRM}	120 V
$T_j(\text{max})$	175 °C
$V_F(\text{typ})$	0.57 V

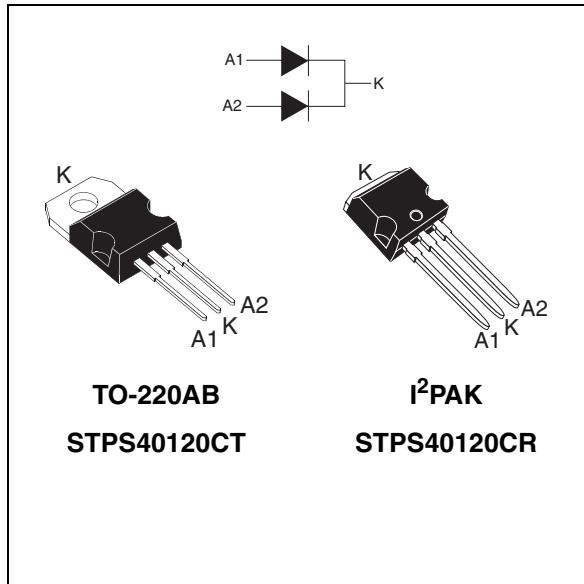
Feature and benefits

- High junction temperature capability
- Avalanche rated
- Low leakage current
- Good trade-off between leakage current and forward voltage drop

Description

Dual center tap Schottky rectifier suited for high frequency Switch Mode Power Supply.

Packaged in TO-220AB and I²PAK, this device is intended to be used in notebook and LCD adaptors, desktop SMPS, providing in these applications a margin between the remaining voltages applied on the diode and the voltage capability of the diode.



Order code

Part Number	Marking
STPS40120CT	STPS40120CT
STPS40120CR	STPS40120CR

Table 1. Absolute ratings (limiting values, per diode)

Symbol	Parameter			Value	Unit
V_{RRM}	Repetitive peak reverse voltage			120	V
$I_{F(\text{RMS})}$	RMS forward voltage			30	A
$I_{F(AV)}$	Average forward current	$\delta = 0.5$ $T_c = 145^\circ \text{C}$	Per diode Per device	20 40	A
I_{FSM}	Surge non repetitive forward current	$t_p = 10 \text{ ms}$ Sinusoidal		200	A
P_{ARM}	Repetitive peak avalanche power	$t_p = 1 \mu\text{s}$ $T_j = 25^\circ \text{C}$		10500	W
T_{stg}	Storage temperature range			-65 to + 175	°C
T_j	Maximum operating junction temperature ⁽¹⁾			175	°C

1. $\frac{dP_{tot}}{dT_j} < \frac{1}{R_{th(j-a)}}$ condition to avoid runaway for a diode on its own heatsink

1 Characteristics

Table 2. Thermal parameters

Symbol	Parameter		Value	Unit
$R_{th(j-c)}$	Junction to case	Per diode	1.6	° C/W
		Total	0.85	
$R_{th(c)}$	Coupling	Total	0.1	° C/W

When the diodes 1 and 2 are used simultaneously :

$$\Delta T_j(\text{diode 1}) = P(\text{diode 1}) \times R_{th(j-c)}(\text{per diode}) + P(\text{diode 2}) \times R_{th(c)}$$

Table 3. Static electrical characteristics (per diode)

Symbol	Test conditions			Min.	Typ.	Max.	Unit
$I_R^{(1)}$	Reverse leakage current	$T_j = 25^\circ \text{C}$	$V_R = V_{RRM}$			25	μA
		$T_j = 125^\circ \text{C}$			4	12	mA
$V_F^{(2)}$	Forward voltage drop	$T_j = 25^\circ \text{C}$	$I_F = 7.5 \text{ A}$			0.73	V
		$T_j = 125^\circ \text{C}$			0.57	0.61	
		$T_j = 25^\circ \text{C}$	$I_F = 20 \text{ A}$			0.9	
		$T_j = 125^\circ \text{C}$			0.69	0.73	
		$T_j = 25^\circ \text{C}$	$I_F = 40 \text{ A}$			1	
		$T_j = 125^\circ \text{C}$			0.83	0.88	

1. Pulse test : $t_p = 5 \text{ ms}$, $\delta < 2\%$

2. Pulse test : $t_p = 380 \mu\text{s}$, $\delta < 2\%$

To evaluate the maximum conduction losses use the following equation :

$$P = 0.58 \times I_{F(AV)} + 0.0075 I_F^2(\text{RMS})$$

Figure 1. Average forward power dissipation versus average forward current (per diode)

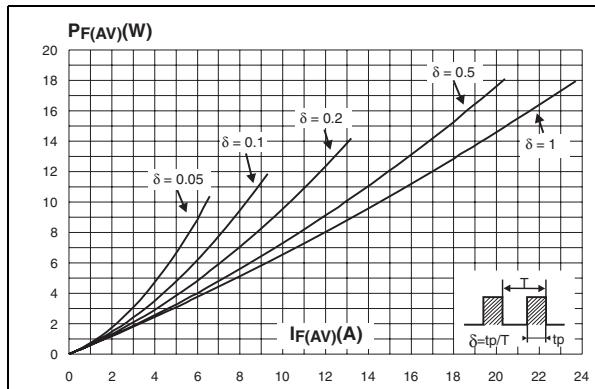


Figure 2. Average forward current versus ambient temperature ($\delta = 0.5$, per diode)

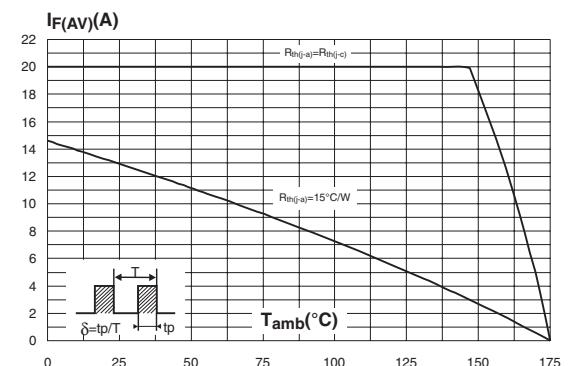


Figure 3. Normalized avalanche power derating versus pulse duration

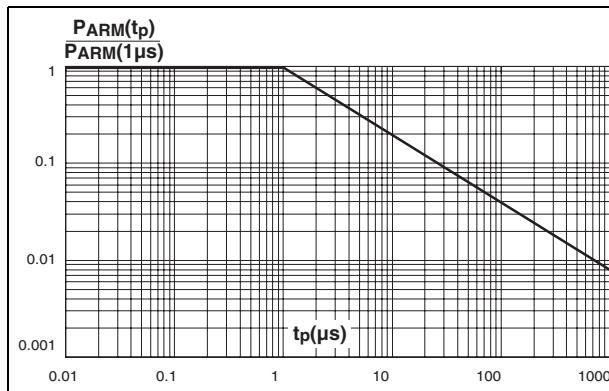


Figure 4. Normalized avalanche power derating versus junction temperature

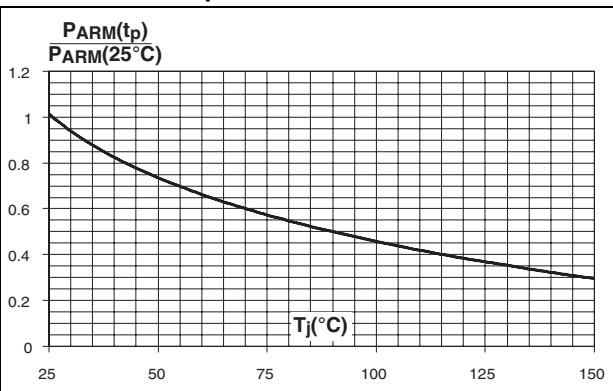


Figure 5. Non repetitive surge peak forward current versus overload duration (maximum values, per diode)

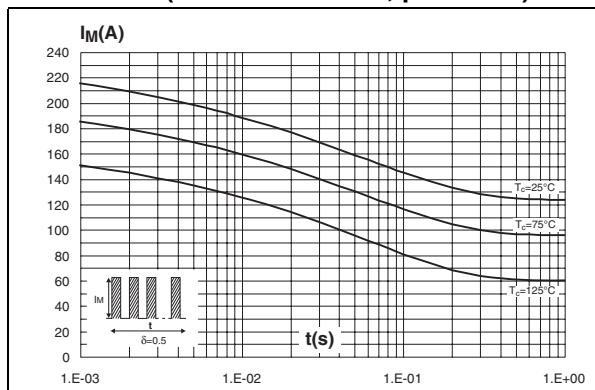
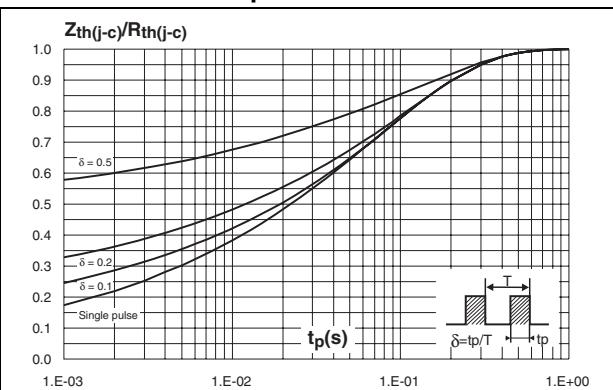


Figure 6. Relative variation of thermal impedance junction to ambient versus pulse duration



3 Ordering information

Ordering type	Marking	Package	Weight	Base qty	Delivery mode
STPS40120CT	STPS40120CT	TO-220AB	2.23 g	50	Tube
STPS40120CR	STPS40120CR	I ² PAK	1.49 g	50	Tube

4 Revision history

Date	Revision	Description of Changes
18-Feb-2005	1	First issue
1-Dec-2006	2	Reformatted to current standards. Added I ² PAK.